

isc N-Channel MOSFET Transistor

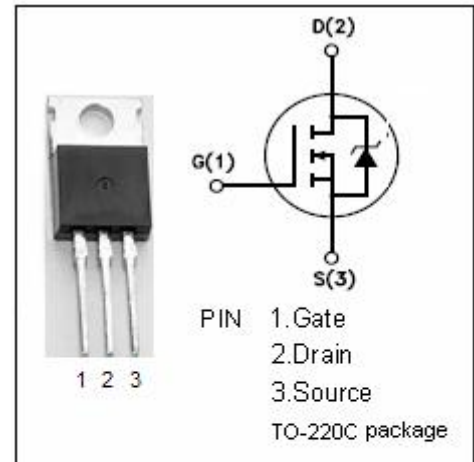
2SK858

DESCRIPTION

- Drain Current $-I_D=2A @ T_C=25^\circ C$
- Drain Source Voltage-
: $V_{DSS}=600V(\text{Min})$

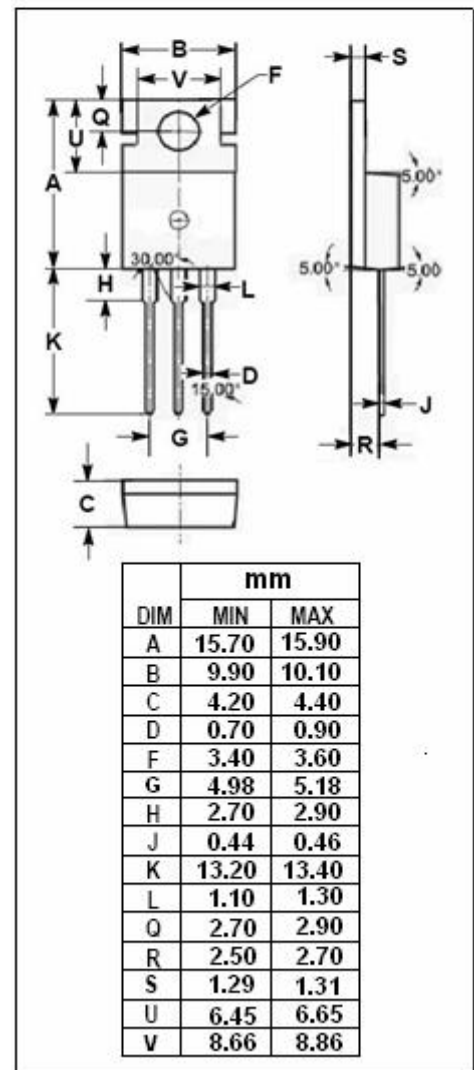
APPLICATIONS

- Designed for high voltage, high speed power switching applications such as switching regulators, converters, solenoid and relay drivers.



ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

SYMBOL	ARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage ($V_{GS}=0$)	600	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current-continuous@ $TC=25^\circ C$	2	A
P_{tot}	Total Dissipation@ $TC=25^\circ C$	40	W
T_j	Max. Operating Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-55~150	$^\circ C$



THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance,Junction to Case	1.67	$^\circ C/W$
$R_{th j-a}$	Thermal Resistance,Junction to Ambient	62.5	$^\circ C/W$

isc N-Channel Mosfet Transistor**2SK858****• ELECTRICAL CHARACTERISTICS (T_C=25°C)**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0; I _D = 10mA	600			V
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} =0; I _D = 1mA	2.0		4.0	V
R _{DS(ON)}	Drain-Source On-stage Resistance	V _{GS} = 10V; I _D =1A			4.0	Ω
I _{GSS}	Gate Source Leakage Current	V _{GS} = ±20V; V _{DS} = 0			±100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =600V; V _{GS} = 0			0.1	mA